



**THE DATASHEET OF  
AO4435L\_102**



### General Description

The AO4435 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications.

- RoHS Compliant
- AO4435 is Halogen Free

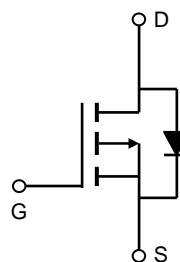
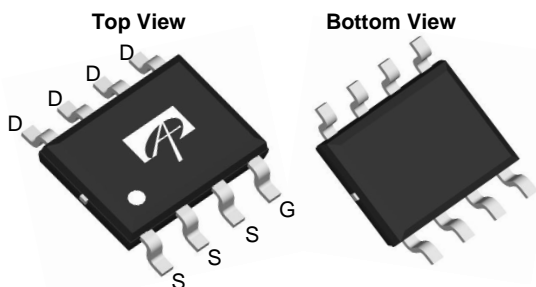
### Product Summary

$V_{DS} = -30V$   
 $I_D = -10.5A$  ( $V_{GS} = -20V$ )  
 $R_{DS(ON)} < 14m\Omega$  ( $V_{GS} = -20V$ )  
 $R_{DS(ON)} < 18m\Omega$  ( $V_{GS} = -10V$ )  
 $R_{DS(ON)} < 36m\Omega$  ( $V_{GS} = -5V$ )

100% UIS Tested  
 100% Rg Tested



SOIC-8



### Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

| Parameter                                      | Symbol         | Maximum          | Units      |
|--|----------------|------------------|------------|
| Drain-Source Voltage                           | $V_{DS}$       | -30              | V          |
| Gate-Source Voltage                            | $V_{GS}$       | $\pm 25$         | V          |
| Continuous Drain Current <sup>A</sup>          | $I_D$          | $T_A=25^\circ C$ | -10.5      |
|  |                | $T_A=70^\circ C$ | -8         |
| Pulsed Drain Current <sup>B</sup>              | $I_{DM}$       | -80              | A          |
| Power Dissipation <sup>A</sup>                 | $P_D$          | $T_A=25^\circ C$ | 3.1        |
|  |                | $T_A=70^\circ C$ | 2.0        |
| Avalanche Current <sup>B</sup>                 | $I_{AR}$       | -20              | A          |
| Repetitive avalanche energy 0.3mH <sup>B</sup> | $E_{AR}$       | 60               | mJ         |
| Junction and Storage Temperature Range         | $T_J, T_{STG}$ | -55 to 150       | $^\circ C$ |

### Thermal Characteristics

| Parameter                                | Symbol          | Typ          | Max | Units        |
|--|-----------------|--------------|-----|--------------|
| Maximum Junction-to-Ambient <sup>A</sup> | $R_{\theta JA}$ | $t \leq 10s$ | 32  | $^\circ C/W$ |
|  |                 | Steady State | 60  | $^\circ C/W$ |
| Maximum Junction-to-Lead <sup>C</sup>    | $R_{\theta JL}$ | 17           | 24  | $^\circ C/W$ |

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

| Symbol                      | Parameter                             | Conditions   | Min  | Typ   | Max       | Units         |
|-----------------------------|---------------------------------------|--|------|-------|-----------|---------------|
| <b>STATIC PARAMETERS</b>    |                                       |  |      |       |           |               |
| $BV_{DSS}$                  | Drain-Source Breakdown Voltage        | $I_D = -250\mu\text{A}$ , $V_{GS} = 0\text{V}$                                       | -30  |       |           | V             |
| $I_{DSS}$                   | Zero Gate Voltage Drain Current       | $V_{DS} = -30\text{V}$ , $V_{GS} = 0\text{V}$<br>$T_J = 55^\circ\text{C}$            |      |       | -1<br>-5  | $\mu\text{A}$ |
| $I_{GSS}$                   | Gate-Body leakage current             | $V_{DS} = 0\text{V}$ , $V_{GS} = \pm 25\text{V}$                                     |      |       | $\pm 100$ | nA            |
| $V_{GS(th)}$                | Gate Threshold Voltage                | $V_{DS} = V_{GS}$ , $I_D = -250\mu\text{A}$  | -1.7 | -2.3  | -3        | V             |
| $I_{D(ON)}$                 | On state drain current                | $V_{GS} = -10\text{V}$ , $V_{DS} = -5\text{V}$                                       | -80  |       |           | A             |
| $R_{DS(ON)}$                | Static Drain-Source On-Resistance     | $V_{GS} = -20\text{V}$ , $I_D = -11\text{A}$<br>$T_J = 125^\circ\text{C}$            |      | 11    | 14        | m $\Omega$    |
|                             |                                       | $V_{GS} = -10\text{V}$ , $I_D = -10\text{A}$   |      | 15    | 19        |               |
|                             |                                       | $V_{GS} = -5\text{V}$ , $I_D = -5\text{A}$   |      | 15    | 18        |               |
|                             |                                       |  |      | 27    | 36        |               |
| $g_{FS}$                    | Forward Transconductance              | $V_{DS} = -5\text{V}$ , $I_D = -10\text{A}$  |      | 22    |           | S             |
| $V_{SD}$                    | Diode Forward Voltage                 | $I_S = -1\text{A}$ , $V_{GS} = 0\text{V}$  |      | -0.74 | -1        | V             |
| $I_S$                       | Maximum Body-Diode Continuous Current |  |      |       | -3.5      | A             |
| <b>DYNAMIC PARAMETERS</b>   |                                       |  |      |       |           |               |
| $C_{ISS}$                   | Input Capacitance                     | $V_{GS}=0\text{V}$ , $V_{DS}=-15\text{V}$ , $f=1\text{MHz}$                          |      | 1130  | 1400      | pF            |
| $C_{OSS}$                   | Output Capacitance                    |  |      | 240   |           | pF            |
| $C_{RSS}$                   | Reverse Transfer Capacitance          |  |      | 155   |           | pF            |
| $R_g$                       | Gate resistance                       | $V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$                            | 1    | 5.8   | 8         | $\Omega$      |
| <b>SWITCHING PARAMETERS</b> |                                       |  |      |       |           |               |
| $Q_{g(10V)}$                | Total Gate Charge                     | $V_{GS}=-10\text{V}$ , $V_{DS}=-15\text{V}$ , $I_D=-10\text{A}$                      |      | 18    | 24        | nC            |
| $Q_{g(4.5V)}$               | Total Gate Charge                     |  |      | 9.5   |           |               |
| $Q_{gs}$                    | Gate Source Charge                    |  |      | 5.5   |           | nC            |
| $Q_{gd}$                    | Gate Drain Charge                     |  |      | 3.3   |           | nC            |
| $t_{D(on)}$                 | Turn-On DelayTime                     | $V_{GS}=-10\text{V}$ , $V_{DS}=-15\text{V}$ , $R_L=1.5\Omega$ ,<br>$R_{GEN}=3\Omega$ |      | 8.7   |           | ns            |
| $t_r$                       | Turn-On Rise Time                     |  |      | 8.5   |           | ns            |
| $t_{D(off)}$                | Turn-Off DelayTime                    |  |      | 18    |           | ns            |
| $t_f$                       | Turn-Off Fall Time                    |  |      | 7     |           | ns            |
| $t_{rr}$                    | Body Diode Reverse Recovery Time      | $I_F=-10\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$                                  |      | 25    | 30        | ns            |
| $Q_{rr}$                    | Body Diode Reverse Recovery Charge    | $I_F=-10\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$                                  |      | 12    |           | nC            |

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using  $<300\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

F: The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

G:  $E_{AR}$  and  $I_{AR}$  ratings are based on low frequency and duty cycles to keep  $T_J=25^\circ\text{C}$ .

Rev7: Nov. 2010

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

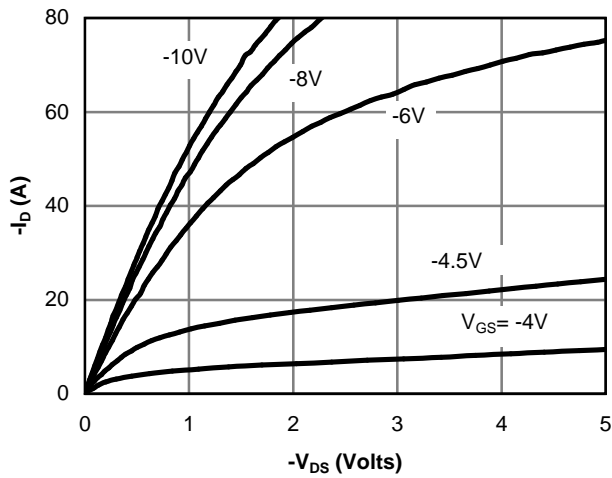


Figure 1: On-Region Characteristics

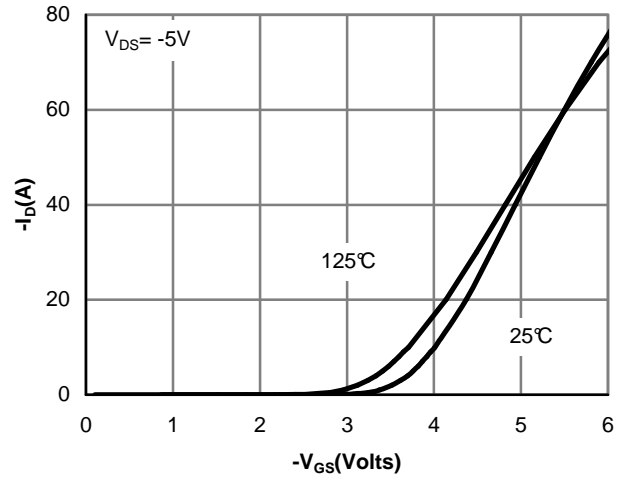


Figure 2: Transfer Characteristics

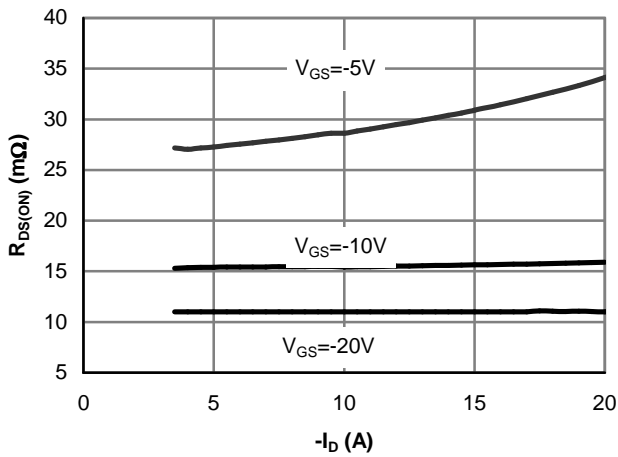


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

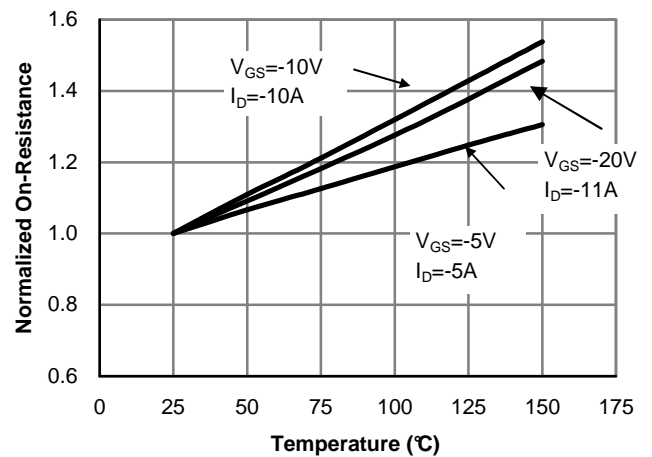


Figure 4: On-Resistance vs. Junction Temperature

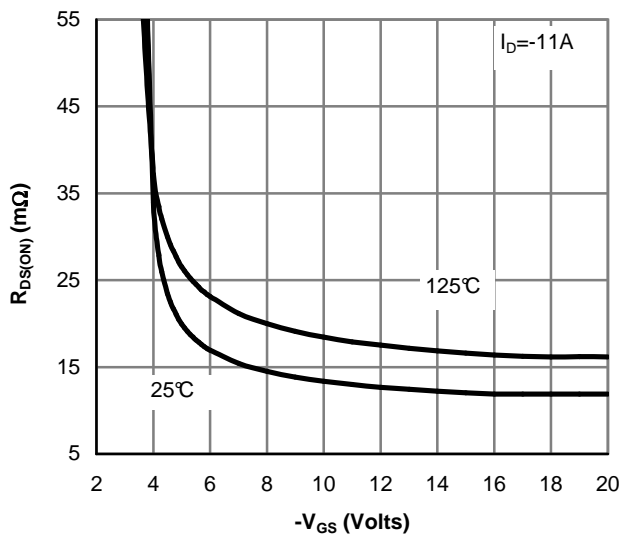


Figure 5: On-Resistance vs. Gate-Source Voltage

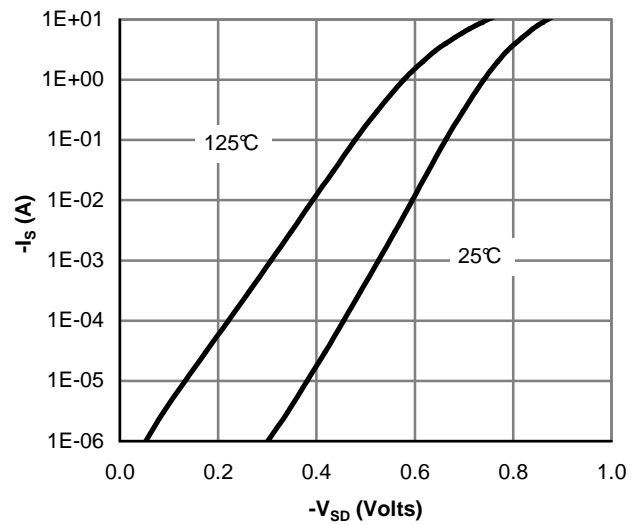


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

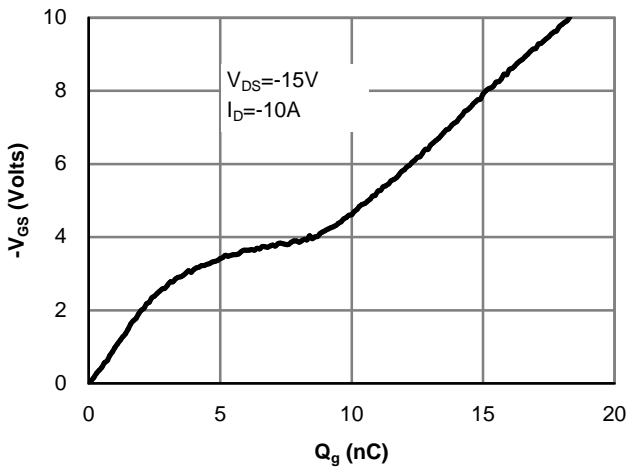


Figure 7: Gate-Charge Characteristics

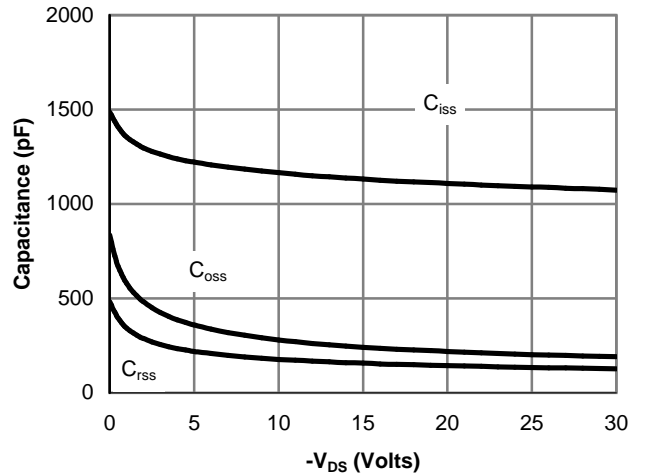


Figure 8: Capacitance Characteristics

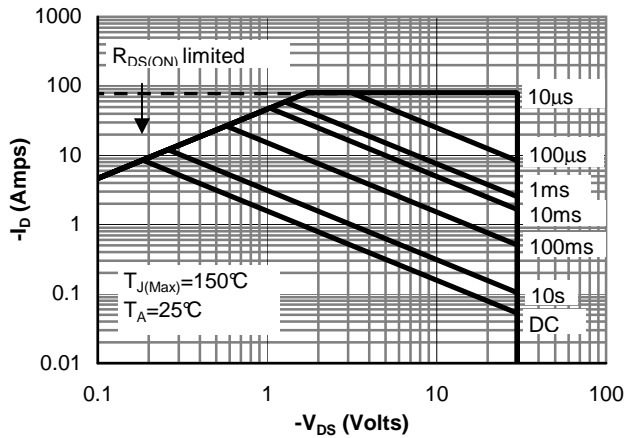


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

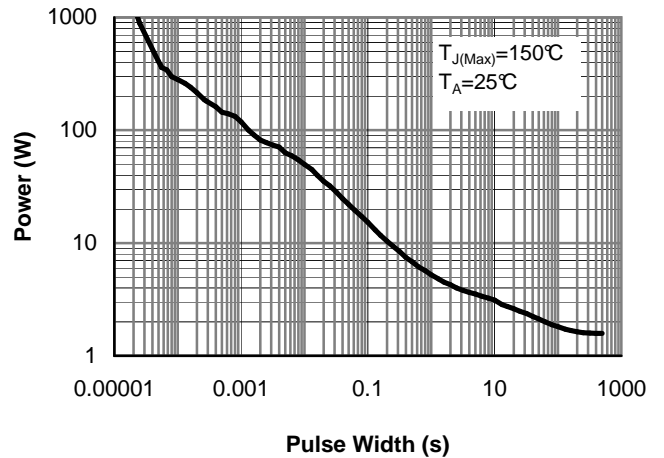


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

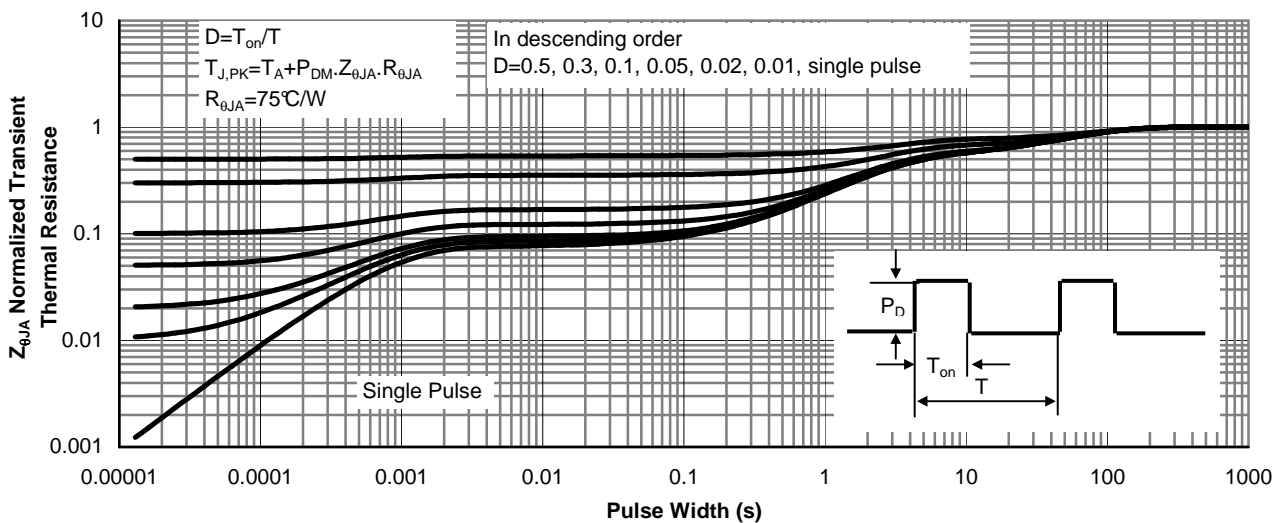
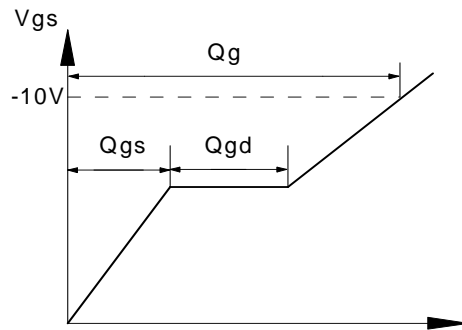
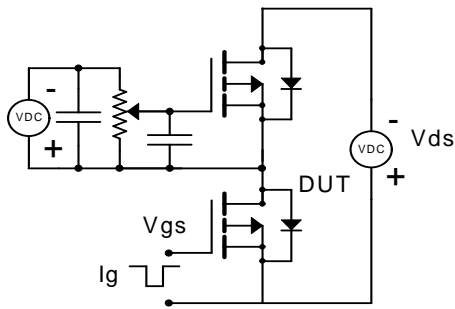
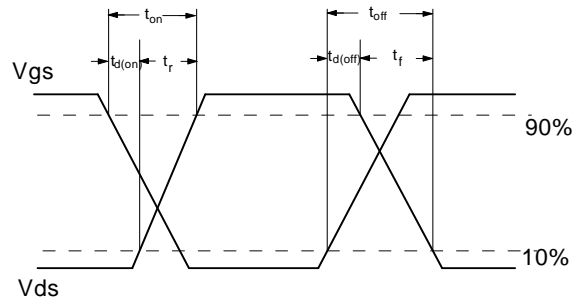
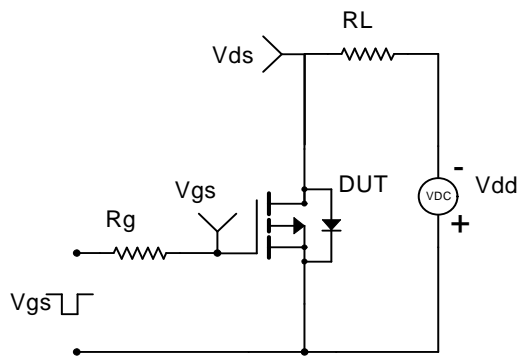


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)

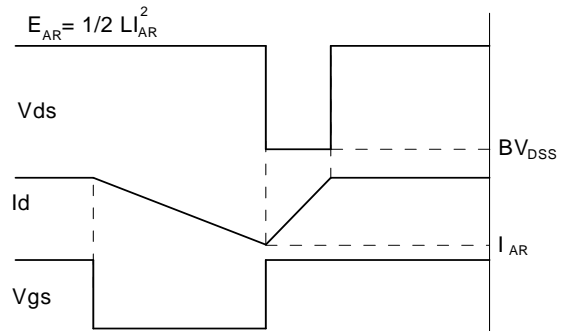
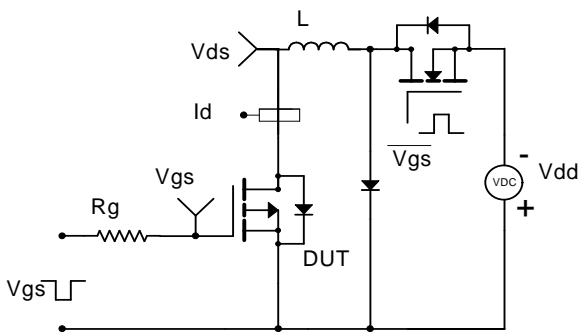
Gate Charge Test Circuit & Waveform



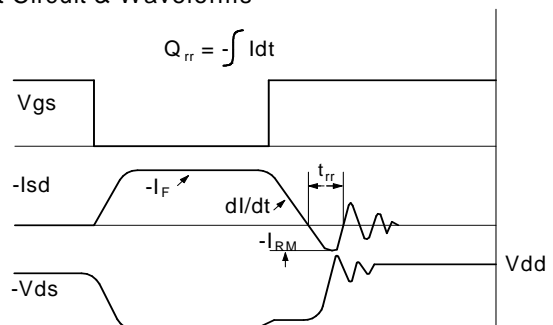
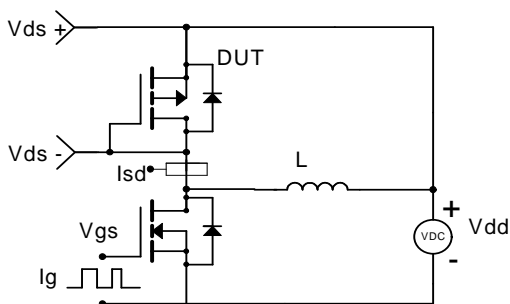
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



## Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

- [View AO4435L\\_102 on WIN SOURCE](#)
- [Alpha & Omega Semiconductor Inc. Information](#)

## Optimize Your Supply Chain with WIN SOURCE Solutions

- ✓ Global Sourcing Solution
- ✓ Obsolete Management
- ✓ Cost Control Management
- ✓ Shortage Management
- ✓ Alternative Solution
- ✓ Excess Inventory Management